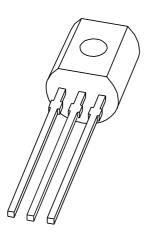
DISCRETE SEMICONDUCTORS

DATA SHEET



PSS9015B PNP general purpose transistor

Product specification

2002 Sep 20





PNP general purpose transistor

PSS9015B

FEATURES

• Low collector capacitance.

APPLICATIONS

- General purpose switching and amplification
- Low frequency, low noise amplifier.

DESCRIPTION

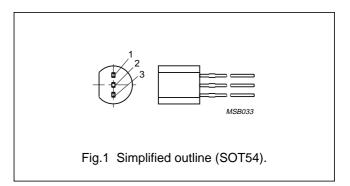
PNP transistor in a SOT54 plastic package. NPN complement: PSS9014.

MARKING

TYPE NUMBER	MARKING CODE
PSS9015B	S9015B

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V_{CEO}	collector-emitter voltage	open base	_	-45	٧
V _{EBO}	emitter-base voltage	open collector	_	- 5	٧
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		_	-200	mA
P _{tot}	total power dissipation	up to T _{amb} = 25 °C; note 1	_	500	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	in free air; note 1	240	K/W
'	ambient			

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0$	_	_	-50	nA
		$V_{CB} = -30 \text{ V}; I_E = 0;$ $T_{amb} = 150 \text{ °C}$	_	-	- 5	μΑ
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0$	_	_	-100	nA
h _{FE}	DC current gain	$I_C = -1 \text{ mA}; V_{CE} = -5 \text{ V}$	100	200	300	
V _{CEsat}	saturation voltage	$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}; \text{ note } 1$	_	_	-700	mV
V _{BEsat}	saturation voltage	$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}; \text{ note } 1$	_	_	-1000	mV
V _{BEon}	base-emitter turn-on voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-600	_	-750	mV
f _T	transition frequency	I _C = -10 mA; V _{CE} = -10 V; f = 100 MHz	100	-	_	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0;$ f = 1 MHz	_	_	7	pF
F	noise figure	$V_{CE} = -5 \text{ V}; I_{C} = -0.2 \text{ mA};$ $R_{S} = 1 \text{ k}\Omega; f = 1 \text{ kHz}; B = 200 \text{ Hz}$	_	_	10	dB

Note

1. Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$

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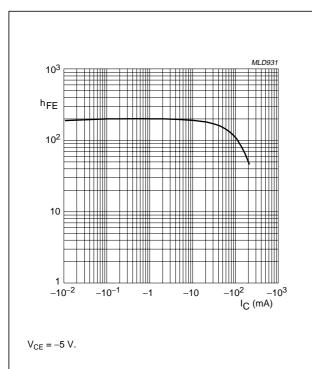
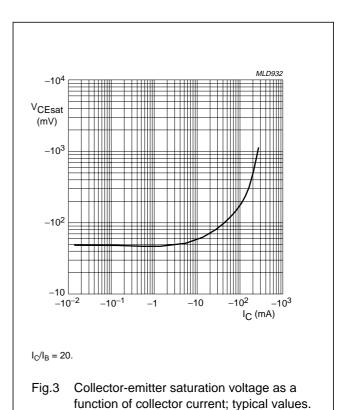
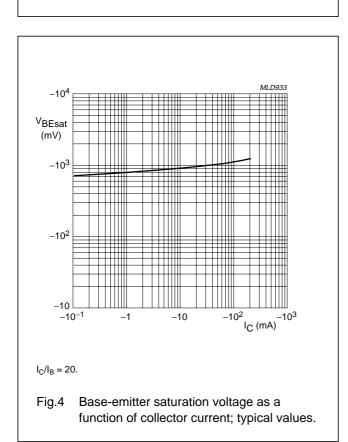
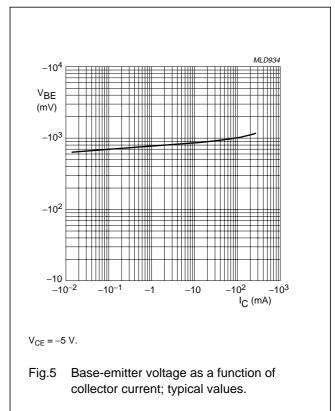


Fig.2 DC current gain as a function of collector current; typical values.







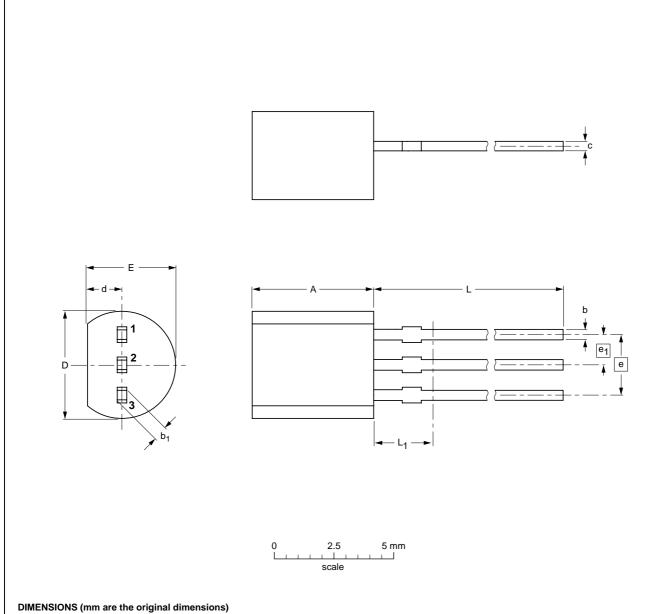
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFERENCES			EUROPEAN		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT54		TO-92	SC-43			97-02-28	

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PNP general purpose transistor

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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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